Abstracts

A Technique for Deriving Noise-Parameters of Millimeter-Wave Low-Noise HEMTs and its Application to MMIC LNA Design

H. Yoshinaga, Y. Kashiwabara, B. Abe and K. Shibata. "A Technique for Deriving Noise-Parameters of Millimeter-Wave Low-Noise HEMTs and its Application to MMIC LNA Design." 1996 MTT-S International Microwave Symposium Digest 96.1 (1996 Vol. I [MWSYM]): 25-28.

An on-wafer tuning method has been applied to derive noise parameters of pseudomorphic HEMTs measured at W-Band and K-Band. As an application of the method, a K-Band MMIC LNA with 1.6 dB NF and greater than 32 dB gain has been successfully developed.

❏ Return to main document.

Click on title for a complete paper.